L	Hits	Search Text	DB	Time stamp
Number		(115.042.02011) DV		
1	2	("5942032").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/04/13 17:02
2	1262	((117/13) or (117/19) or (117/21) or (117/34)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/04/13 17:02
3	17	(((117/13) or (117/19) or (117/21) or (117/34)).CCLS.) and (hydrogen or "H.sub.2") near20 (pressure or vacuum)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/04/13 17:04
4	13	((((117/13) or (117/19) or (117/21) or (117/34)).CCLS.) and (hydrogen or "H.sub.2") near20 (pressure or vacuum) and czochralski	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/04/13 17:13
5	455	(257/620).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/04/13 17:14
6	362	(438/906).CCLS.	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/04/13 17:14
7	0	(437/83).CCLS.	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/04/13 17:14
8	0	(437/84).CCLS.	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/04/13 17:15
9	413	(117/84).CCLS.	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/04/13 17:15
10	1229	((257/620).CCLS.) or ((438/906).CCLS.) or ((437/83).CCLS.) or ((437/84).CCLS.)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/04/13 17:15
11	4	(((257/620).CCLS.) or ((438/906).CCLS.) or ((437/83).CCLS.) or ((437/84).CCLS.) or ((117/84).CCLS.)) and czochralski and (hydrogen or "H.sub.2") near15 (vacuum or pressure)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/04/13 17:16
-	1154	((257/620) or (438/906) or (437/83) or (437/84) or (117/19) or (117/84)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/04/11 18:01
-	1	((("257/620") or ("438/906") or ("437/83") or ("437/84") or ("117/19") or ("117/84")).CCLS.) and (hydrogen with dop\$3 with silicon with wafer) same concentration	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/01/05 19:09

_	90	((("257/620") or ("438/906") or ("437/83") or ("437/84") or ("117/19") or	USPAT; US-PGPUB;	2002/01/05 19:10
		("117/84")).CCLS.) and czochralski	EPO; JPO;	19:10
			DERWENT;	
_	18	((("257/620") or ("438/906") or	IBM_TDB USPAT;	2002/01/05
		("437/83") or ("437/84") or ("117/19") or	US-PGPUB;	19:11
		("117/84")).CCLS.) and heat adj shield	EPO; JPO;	
			DERWENT; IBM TDB	
-	37		USPAT;	2002/01/05
		("437/83") or ("437/84") or ("117/19") or ("117/84")).CCLS.) and nitrogen with	US-PGPUB;	19:11
		dop\$3	EPO; JPO; DERWENT;	
			IBM_TDB	
_	43	((("257/620") or ("438/906") or ("437/83") or ("437/84") or ("117/19") or	USPAT; US-PGPUB;	2002/01/05
		("117/84")).CCLS.) and (argon with	EPO; JPO;	19:12
		hydrogen)	DERWENT;	
_	201	((("257/620") or ("438/906") or	IBM_TDB USPAT;	2002/01/05
		("437/83") or ("437/84") or ("117/19") or	US-PGPUB;	19:12
		("117/84")).CCLS.) and oxidation	EPO; JPO;	
			DERWENT; IBM TDB	
-	1		USPAT;	2002/01/05
		czochralski.ti,ab. and nitrogen.ti,ab.	US-PGPUB;	19:14
			EPO; JPO; DERWENT;	
			IBM_TDB	
_	54	silicon adj single adj crystal.ti,ab. and czochralski.ti,ab. and nitrogen.ti,ab.	USPAT; US-PGPUB;	2002/01/05
		observations. and interogeneer, and	EPO; JPO;	19:14
	1		DERWENT;	
_	805	(117/13).CCLS.	<pre>IBM_TDB USPAT;</pre>	2002/01/05
		(,,	US-PGPUB;	19:17
			EPO; JPO;	
			DERWENT; IBM TDB	
-	0	(("117/13").CCLS.) and heat adj	USPĀT;	2002/01/05
		sjield.ti,ab. and czochralski	US-PGPUB; EPO; JPO;	19:17
			DERWENT;	
_		(("117/13").CCLS.) and heat adj	IBM_TDB	
	3	shield.ti,ab. and czochralski	USPAT; US-PGPUB;	2002/01/05 19:17
			EPO; JPO;	
			DERWENT;	
-	43	trench adj mosfet.ti.	<pre>IBM_TDB USPAT;</pre>	2002/01/05
			US-PGPUB;	20:15
			EPO; JPO; DERWENT;	
			IBM_TDB	
-	9	(trench adj mosfet.ti.) and 257/\$6.ccls.	USPAT;	2002/01/05
			US-PGPUB; EPO; JPO;	20:15
			DERWENT;	
	4	"6191009"	IBM_TDB USPAT;	2002/01/20
	7	0252005	US-PGPUB;	2002/01/29 12:24
			EPO; JPO;	
			DERWENT;	
-	5	(("6191009") or ("6299982") or	IBM_TDB USPAT	2002/01/29
		("5942032") or ("6224668") or		12:25
_	5	("6197109")).PN. (("6191009") or ("6299982") or	USPAT	2002/02/01
		("5942032") or ("6244668") or	ODEMI	11:22
		("6197109")).PN.		

		/#G004GG0#)		
-	1	("6224668").PN.	USPAT	2002/02/01 11:29
-	4	("4210486").PN.	USPAT;	2002/06/11
			US-PGPUB;	16:22
1			EPO; JPO; DERWENT;	
			IBM TDB	
-	410		USPAT;	2002/06/11
		lcd).ti. and 257/\$6.ccls.	US-PGPUB;	16:23
			EPO; JPO; DERWENT;	
			IBM TDB	
_	64	method.clm. and silicon.ti, ab. and	USPAT;	2002/06/19
		wafer.clm. and melt.clm. and (h or hydrogen).clm. and (pressure near4 mbar)	US-PGPUB; EPO; JPO;	17:56
		(nitrogen near4 (doping or dopant or	DERWENT;	
		doped or dope)) and	IBM_TDB	
_	64	czochralski.ti,ab,clm. method.clm. and silicon.ti,ab. and	USPAT;	2002/06/19
		wafer.clm. and melt.clm. and	US-PGPUB;	17:59
		hydrogen.clm. and (pressure near4 mbar)	EPO; JPO;	
		(nitrogen near4 (doping or dopant or doped or dope)) and	DERWENT;	
		czochralski.ti,ab,clm.	IBM_TDB	
-	1	method.clm. and silicon.ti,ab. and	USPAT;	2002/06/19
		wafer.clm. and melt.clm. and hydrogen.clm. and (pressure near4 mbar)	US-PGPUB;	18:01
		and (nitrogen near4 (doping or dopant or	EPO; JPO; DERWENT;	
		doped or dope)) and	IBM_TDB	
_	1	czochralski.ti,ab,clm. method.clm. and silicon.ti,ab. and	IIGDAM.	2002/06/12
		wafer.clm. and melt.clm. and (h or	USPAT; US-PGPUB;	2002/06/19 18:02
		hydrogen).clm. and (pressure near4 mbar)	EPO; JPO;	10102
	i	and (nitrogen near4 (doping or dopant or doped or dope)) and	DERWENT;	
		czochralski.ti,ab,clm.	IBM_TDB	
-	1	method.clm. and silicon.ti,ab. and	USPAT;	2002/06/19
		<pre>wafer.clm. and (h or hydrogen).clm. and (pressure near4 mbar) and (nitrogen near4</pre>	US-PGPUB;	18:03
		(doping or dopant or doped or dope)) and	EPO; JPO; DERWENT;	
	_	czochralski.ti,ab,clm.	IBM_TDB	
_	1	method.clm. and silicon.ti,ab. and (h or hydrogen).clm. and (pressure near4 mbar)	USPAT;	2002/06/19
		and (nitrogen near4 (doping or dopant or	US-PGPUB; EPO; JPO;	18:03
		doped or dope)) and	DERWENT;	
_	1	czochralski.ti,ab,clm.	IBM_TDB	2002/06/20
		silicon.ti,ab. and (h or hydrogen).clm. and (pressure near4 mbar) and (nitrogen	USPAT; US-PGPUB;	2002/06/19 18:04
		near4 (doping or dopant or doped or	EPO; JPO;	
		dope)) and czochralski.ti,ab,clm.	DERWENT;	
-	1	silicon and (h or hydrogen).clm. and	IBM_TDB USPAT;	2002/06/19
		(pressure near4 mbar) and (nitrogen near4	US-PGPUB;	18:05
		(doping or dopant or doped or dope)) and czochralski.ti,ab,clm.	EPO; JPO;	
]		CZOCHIAISKI. CI, AD, CIM.	DERWENT; IBM TDB	
-	1	silicon and (h or hydrogen) and (pressure	USPAT;	2002/06/19
		near4 mbar) and (nitrogen near4 (doping or dopant or doped or dope)) and	US-PGPUB;	18:06
		czochralski.ti,ab,clm.	EPO; JPO; DERWENT;	
			IBM_TDB	
-	1	silicon and (h or hydrogen) and (pressure	USPAT;	2002/06/19
		near4 mbar) and (nitrogen near4 (doping or dopant or doped or dope)) and	US-PGPUB; EPO; JPO;	18:06
		czochralski	DERWENT;	
	4		IBM_TDB	
-	1	silicon and (h or hydrogen) and (pressure near5 mbar) and (nitrogen near5 (doping	USPAT; US-PGPUB;	2002/06/19
		or dopant or doped or dope)) and	EPO; JPO;	18:07
		czochralski	DERWENT;	
			IBM_TDB	

-	22	silicon and (h or hydrogen) and pressure	USPAT;	2002/06/19
		and (nitrogen near5 (doping or dopant or	US-PGPUB;	19:20
		doped or dope)) and czochralski	EPO; JPO;	
			DERWENT;	
l _	5	ggoghralaki and massaura assault	IBM_TDB	
-	1	czochralski and pressure near3 mbar and oxygen	USPAT;	2002/06/19
		oxygen	US-PGPUB; EPO; JPO;	19:21
			DERWENT;	
			IBM TDB	
_	23	czochralski.ti,ab. and pressure near3	USPAT;	2002/06/19
		argon	US-PGPUB;	20:37
			EPO; JPO;	20.37
			DERWENT;	
			IBM TDB	
-	5	czochralski.ti,ab. and pressure near3	USPAT;	2002/06/19
		argon near3 mbar	US-PGPUB;	20:37
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
_	0		USPAT;	2002/06/19
		argon near3 mbar near3 hydrogen	US-PGPUB;	20:38
			EPO; JPO;	
			DERWENT;	
_	3	czochralski.ti,ab. and pressure near3	IBM_TDB	2002/06/10
		mbar near3 hydrogen	USPAT; US-PGPUB;	2002/06/19
		mai nears marogen	EPO; JPO;	20:38
			DERWENT;	
	j		IBM TDB	
-	3	czochralski.ti,ab. and pressure near3	USPAT;	2002/06/19
]	mbar near3 hydrogen and silicon.ti,ab.	US-PGPUB;	20:39
ı		-	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
_	3	czochralski.ti,ab. and pressure near3	USPAT;	2002/06/19
		mbar near3 argon and silicon.ti,ab.	US-PGPUB;	20:39
			EPO; JPO;	i
			DERWENT;	
_	13	czochralski and (noble or inert or argon)	IBM_TDB	2002/06/20
		near4 mbar	USPAT; US-PGPUB;	2002/06/20 13:51
ļ			EPO; JPO;	13.31
			DERWENT;	
			IBM TDB	
-	2	("6291874").PN.	USPAT;	2002/06/20
			US-PGPUB;	14:11
			EPO; JPO;	
			DERWENT;	
_		/# (200002#) PM	IBM_TDB	
-	2	("6299892").PN.	USPAT;	2002/06/20
			US-PGPUB;	15:37
	l		EPO; JPO;	
			DERWENT;	
_	3	(zone-drawing or zone adj drawing) near12	IBM_TDB USPAT;	2002/06/20
	١	czochralski	USPAT; US-PGPUB;	2002/06/20 16:07
	ļ		EPO; JPO;	10.07
			DERWENT;	
			IBM TDB	
-	6	(("6291874") or ("4330361")).PN.	USPAT;	2002/06/20
	· ·		US-PGPUB;	16:07
			EPO; JPO;	
	İ		DERWENT;	
		/# COO4 0 T 4 H)	IBM_TDB	
-	2	("6291874").PN.	USPAT;	2002/12/05
			US-PGPUB;	20:43
ļ	İ		EPO; JPO;	
ľ			DERWENT;	
	L		IBM_TDB	

-	3	("4330361").PN.	USPAT;	2002/12/05
			US-PGPUB;	21:05
			EPO; JPO;	
			DERWENT;	
1_	41	nulling near agachuslahi masula	IBM_TDB	
1	71	pulling near3 czochralski near12 melting	USPAT;	2002/12/05
1			US-PGPUB;	21:13
			EPO; JPO;	
			DERWENT;	
_	0	pulling near12 czochralski near12 melting	IBM_TDB USPAT;	2002/12/05
		near12 pressure	US-PGPUB;	21:13
			EPO; JPO;	21.13
			DERWENT;	
			IBM TDB	
-	1		USPAT;	2002/12/05
		near17 pressure	US-PGPUB;	21:13
			EPO; JPO;	
			DERWENT;	
<u> </u>		(#C30000CH) PV	IBM_TDB	
-	2	("6388286").PN.	USPAT;	2002/12/06
1			US-PGPUB;	12:18
			EPO; JPO;	
İ			DERWENT;	
_	2	("6194283").PN.	IBM_TDB	2002 (12 (06
		, , , , , , , , , , , , , , , , , , , ,	USPAT; US-PGPUB;	2002/12/06
			EPO; JPO;	12:10
			DERWENT;	
			IBM TDB	
-	2	("4890144").PN.	USPAT;	2002/12/06
			US-PGPUB;	12:20
			EPO; JPO;	
	i		DERWENT;	
		/#C202000#\\ P**	IBM_TDB	
_	2	("6323090").PN.	USPAT;	2002/12/06
			US-PGPUB;	12:20
			EPO; JPO;	
			DERWENT;	
_	0	("hydrogen near2 pressure and	IBM_TDB USPAT;	2003/04/11
		czochralski.it,ab.").PN.	US-PGPUB;	18:01
		, ,	EPO; JPO;	10.01
			DERWENT;	
			IBM TDB	
_	4	hydrogen near2 pressure and	USPAT;	2003/04/11
		czochralski.ti,ab.	US-PGPUB;	18:02
			EPO; JPO;	
			DERWENT;	
_	5	(single-crystalling or	IBM_TDB	0000 (04 (55
	, ,	(single-crystalline or single-crystal).ti,ab,clm. and stacking	USPAT;	2003/04/12
		adj fault.ti,ab,clm. and (pressure or	US-PGPUB;	13:33
		vacuum) and (hydrogen or "H.sub.2")	EPO; JPO; DERWENT;	
			IBM TDB	
	185	(single-crystalline or	USPAT;	2003/04/12
]	single-crystal).ti,ab,clm. and (growth or	US-PGPUB;	13:34
İ		growing).ti,ab,clm. and (pressure or	EPO; JPO;	
		vacuum) and (hydrogen or "H.sub.2")	DERWENT;	
			IBM_TDB	
-	0	(single-crystalline or	USPAT;	2003/04/12
	[single-crystal).ti,ab,clm. and (growth or	US-PGPUB;	13:35
	1	growing).ti,ab,clm. and (pressure or	EPO; JPO;	
		vacuum) and (hydrogen or "H.sub.2")	DERWENT;	
_	0	near12 (mbar or Hg)	IBM_TDB	
		(single-crystalline or	USPAT;	2003/04/12
		single-crystal).ti,ab,clm. and (growth or growing) ti ab clm and (programs are	US-PGPUB;	13:35
İ		growing).ti,ab,clm. and (pressure or vacuum) and (hydrogen or "H.sub.2")	EPO; JPO;	
		near12 (mbar or mtorr or Hg)	DERWENT;	
			IBM_TDB	

_	22	single adj crystal or monocrystal).ti,ab,clm. and (growth or growing).ti,ab,clm. and (pressure or	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/04/12 13:36
-	35	vacuum) and (hydrogen or "H.sub.2") near12 (mbar or mtorr or Hg) (single-crystalline or single-crystal or single adj crystal or monocrystal).ti,ab,clm. and (growth or	USPAT; US-PGPUB; EPO; JPO;	2003/04/12 13:37
		growing).ti,ab,clm. and (pressure or vacuum) and (hydrogen or "H.sub.2") near12 (atm or pascal or mbar or mtorr or Hq)	DERWENT; IBM_TDB	
-	0	single adj crystal or monocrystal).ti,ab,clm. and (growth or growing).ti,ab,clm. and (pressure or vacuum) and (hydrogen or "H.sub.2") near12 (atm or pascal or mbar or mtorr or	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/12 13:40
-	1	Hg) and nitrogen near12 (doping or impurity) (single-crystalline or single-crystal or single adj crystal or monocrystal).ti,ab,clm. and (growth or growing).ti,ab,clm. and (pressure or vacuum) and (hydrogen or "H.sub.2") near12 (atm or pascal or mbar or mtorr or Hg) and nitrogen near12 (doping or	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/12
~	1	impurity or doped) (single-crystalline or single-crystal or single adj crystal or monocrystal or czochralski).ti,ab,clm. and (growth or growing).ti,ab,clm. and (pressure or vacuum) and (hydrogen or "H.sub.2") near12 (atm or pascal or mbar or mtorr or	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/12 13:42
_	2	Hg) and nitrogen near12 (doping or impurity or doped) (single-crystalline or single-crystal or single adj crystal or monocrystal or czochralski).ti,ab,clm. and (growth or growing).ti,ab,clm. and (pressure or vacuum) and (hydrogen or "H.sub.2")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/12 13:43
		near15 (atm or pascal or mbar or mtorr or Hg) and ("n.sub.2" or nitrogen) near15 (doping or impurity or doped or impurities)	_	
_	996	(single-crystalline or single-crystal or single adj crystal or monocrystal or czochralski).ti,ab,clm. and (growth or growing).ti,ab,clm. and (pressure or vacuum) and (hydrogen or "H.sub.2")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/04/12 13:44
_	551	(single-crystalline or single-crystal or single adj crystal or monocrystal or czochralski).ti,ab,clm. and (growth or growing).ti,ab,clm. and (pressure or vacuum) and (hydrogen or "H.sub.2") and silicon.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/12 13:44
-	240	(single-crystalline or single-crystal or single adj crystal or monocrystal or czochralski).ti,ab,clm. and (growth or growing).ti,ab,clm. and (pressure or vacuum) and (hydrogen or "H.sub.2").ti,ab,clm. and silicon.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/12 13:45
-		(single-crystalline or single-crystal or single adj crystal or monocrystal or czochralski).ti,ab,clm. and (growth or growing).ti,ab,clm. and (pressure or vacuum) and (hydrogen or "H.sub.2").ti,ab,clm. near20 (mbar or pascal or mtorr) and silicon.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/12 13:48
		of moute, and bilicon.ci, ab, cim.		

-	0		USPAT;	2003/04/12
		growing).ti,ab,clm. and (pressure or	US-PGPUB;	13:49
		vacuum) and (hydrogen or	EPO; JPO;	
		"H.sub.2").ti,ab,clm. near20 (mbar or pascal or mtorr) and silicon.ti,ab,clm.	DERWENT;	
_	0	(czochralski or cz-silicon).ti,ab,clm.	IBM_TDB	2002/04/20
		and (growth or growing).ti,ab,clm. and	USPAT;	2003/04/12
		(pressure or vacuum) and (hydrogen or	US-PGPUB;	13:53
		"H.sub.2").ti,ab,clm. near20 (mbar or	EPO; JPO; DERWENT;	
	İ	pascal or mtorr) and silicon.ti,ab,clm.	IBM TDB	
-	68	(czochralski or cz-silicon and	USPAT;	2003/04/12
		single-crystalline or single-crystal or	US-PGPUB;	13:54
		single adj crystal).ti,ab,clm. and	EPO; JPO;	
		(growth or growing).ti,ab,clm. and	DERWENT;	
	1	(pressure or vacuum) near12 (mbar or	IBM TDB	
		pascal or mtorr) and silicon.ti,ab,clm.	_	
-	1207	(czochralski or cz-silicon and	USPAT;	2003/04/12
1		single-crystalline or single-crystal or	US-PGPUB;	13:55
		single adj crystal).ti,ab,clm. and	EPO; JPO;	
		(growth or growing).ti,ab,clm. and	DERWENT;	
		(pressure or vacuum) near12 (mbar or	IBM_TDB	
		pascal or mtorr) stacking adj fault and		
_	6	silicon.ti,ab,clm. (czochralski or cz-silicon and	Hansa	2002/24/22
		single-crystalline or single-crystal or	USPAT;	2003/04/12
		single-crystalline or single-crystal or single adj crystal).ti,ab,clm. and	US-PGPUB;	13:55
		(growth or growing).ti,ab,clm. and	EPO; JPO; DERWENT;	
		(pressure or vacuum) near12 (mbar or	IBM TDB	
		pascal or mtorr) and stacking adj fault	TDM_TDB	
		and silicon.ti, ab, clm.		
-	2	("5993557").PN.	USPAT;	2003/04/12
		•	US-PGPUB;	14:04
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	23	(cz-silicon or czochralski).ti,ab,clm.	USPAT;	2003/04/12
		and stacking adj fault and (hydrogen or	US-PGPUB;	14:12
<u> </u>		"H.sub.2") and (pressure or vacuum)	EPO; JPO;	
			DERWENT;	
_	6	(cz-silicon or czochralski).ti,ab,clm.	IBM_TDB	2002/04/12
		and stacking adj fault and (hydrogen or	USPAT; US-PGPUB;	2003/04/12 14:07
		"H.sub.2") and (pressure or vacuum) and	EPO; JPO;	14.07
1		"shin-etsu"	DERWENT;	
			IBM TDB	
-	11	(cz-silicon or czochralski).ti,ab,clm.	USPAT;	2003/04/12
		and stacking adj fault and (hydrogen or	US-PGPUB;	14:13
		"H.sub.2") and (pressure or vacuum) and	EPO; JPO;	
		(mbar or bar or atm or pascal or torr or	DERWENT;	
		mtorr)	IBM_TDB	
-	4	(cz-silicon or czochralski).ti,ab,clm.	USPAT;	2003/04/12
		and stacking adj fault and (hydrogen or	US-PGPUB;	14:17
		"H. sub.2") and (pressure or vacuum)	EPO; JPO;	
		near15 (mbar or bar or atm or pascal or torr or mtorr)	DERWENT;	
_	0	(cz-silicon or czochralski).ti,ab,clm.	IBM_TDB	2002/04/12
		and stacking adj fault and (hydrogen or	USPAT;	2003/04/12
		"H.sub.2") near25 (pressure or vacuum)	US-PGPUB;	14:18
		near25 (mbar or bar or atm or pascal or	EPO; JPO; DERWENT;	
		torr or mtorr)	IBM TDB	
-	7	(cz-silicon or czochralski).ti,ab,clm.	USPAT;	2003/04/12
		and (hydrogen or "H.sub.2") near25	US-PGPUB;	14:28
		(pressure or vacuum) near25 (mbar or bar	EPO; JPO;	
		or atm or pascal or torr or mtorr)	DERWENT;	
			IBM TDB	
-	0	stacking adj fault near15 hydrogen near15	USPAT;	2003/04/12
		(mbar or mtorr or pascal)	US-PGPUB;	14:29
		· ·	EPO; JPO;	
			DERWENT;	
			IBM TDB	

	Λ			
-	4	stacking adj fault and hydrogen near15	USPAT;	2003/04/12
		(mbar or mtorr or pascal)	US-PGPUB;	14:30
			EPO; JPO;	
			DERWENT;	
İ			IBM TDB	
-	80	manufactoria and (exocutatori	USPAT;	2003/04/12
		or cz-silicon)	US-PGPUB;	14:31
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
[-]	5	"shin-etsu" and hydrogen near15 pressure	USPAT;	2003/04/12
		and (czochralski or cz-silicon)	US-PGPUB;	14:32
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	5	"shin-etsu" and hydrogen near15 pressure	USPAT;	2003/04/12
		and (czochralski or cz-silicon or cz adj	US-PGPUB;	14:32
		method)	EPO; JPO;	
			DERWENT;	ĺ
			IBM TDB	
-	3	("4330361").PN.	USPAT;	2003/04/12
			US-PGPUB;	18:15
			EPO; JPO;	
			DERWENT;	
			IBM TDB	